

## 1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

## 2. Features and benefits

- High blocking voltage capability
- High noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

## 3. Applications

- General purpose motor control
- General purpose switching

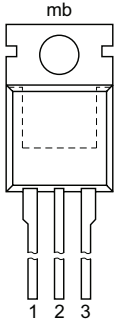
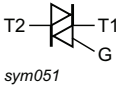
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values				Unit
Absolute maximum rating							
V <sub>DRM</sub>	repetitive peak off-state voltage		800				V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>mb</sub> ≤ 91 °C; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	25				A
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	190				A
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	6	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	10	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	11	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 7</a>		-	23	70	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		
3	G	gate		
mb	T2	mounting base; main terminal 2		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BTA140-800	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

7. Marking

Table 4. Marking codes

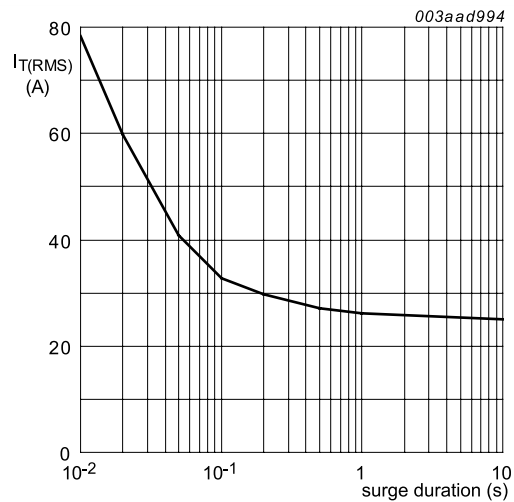
Type number	Marking codes
BT140-800	BT140-800

## 8. Limiting values

**Table 5. Limiting values**

*In accordance with the Absolute Maximum Rating System (IEC 60134).*

Symbol	Parameter	Conditions	Values	Unit
$V_{\text{DRM}}$	repetitive peak off-state voltage		800	V
$I_{\text{T(RMS)}}$	RMS on-state current	full sine wave; $T_{\text{mb}} \leq 91^{\circ}\text{C}$ ; <a href="#">Fig 1</a> ; <a href="#">Fig 2</a> ; <a href="#">Fig 3</a>	25	A
$I_{\text{TSM}}$	non-repetitive peak on-state current	full sine wave; $T_{\text{j(init)}} = 25^{\circ}\text{C}$ ; $t_{\text{p}} = 20 \text{ ms}$ ; <a href="#">Fig 4</a> ; <a href="#">Fig 5</a>	190	A
		full sine wave; $T_{\text{j(init)}} = 25^{\circ}\text{C}$ ; $t_{\text{p}} = 16.7 \text{ ms}$	209	A
$I^2t$	$I^2t$ for fusing	$t_{\text{p}} = 10 \text{ ms}$ ; SIN	180	$\text{A}^2\text{s}$
$dI_{\text{T}}/dt$	rate of rise of on-state current	$I_{\text{G}} = 70 \text{ mA}$ ; T2+ G+	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 70 \text{ mA}$ ; T2+ G-	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 70 \text{ mA}$ ; T2- G-	50	$\text{A}/\mu\text{s}$
		$I_{\text{G}} = 140 \text{ mA}$ ; T2- G+	10	$\text{A}/\mu\text{s}$
$I_{\text{GM}}$	peak gate current		2	A
$P_{\text{GM}}$	peak gate power		5	W
$P_{\text{G(AV)}}$	average gate power	over any 20 ms period	0.5	W
$T_{\text{stg}}$	storage temperature		-40 to 150	$^{\circ}\text{C}$
$T_{\text{j}}$	junction temperature		125	$^{\circ}\text{C}$



$f = 50 \text{ Hz}; T_{mb} = 91^\circ\text{C}$

Fig. 1. RMS on-state current as a function of surge duration; maximum values

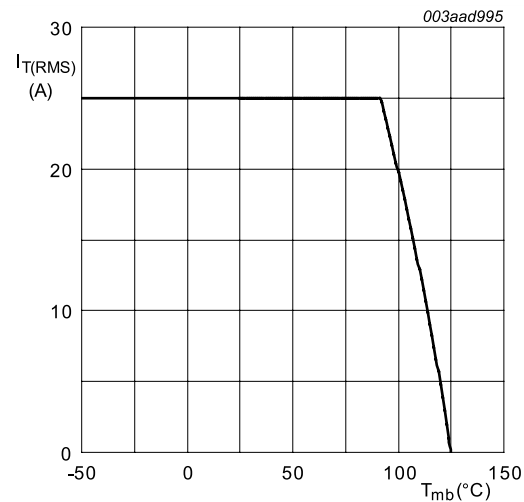
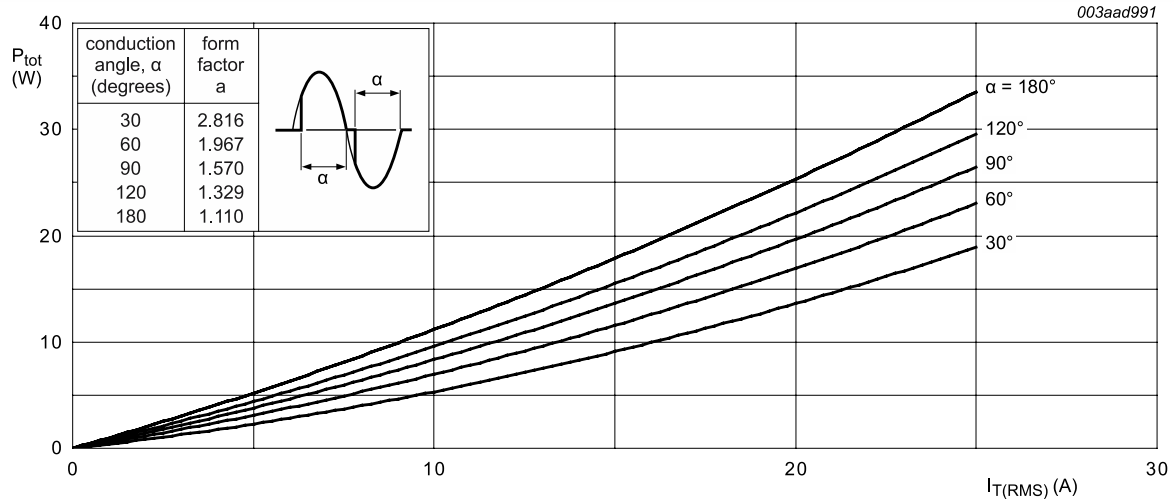
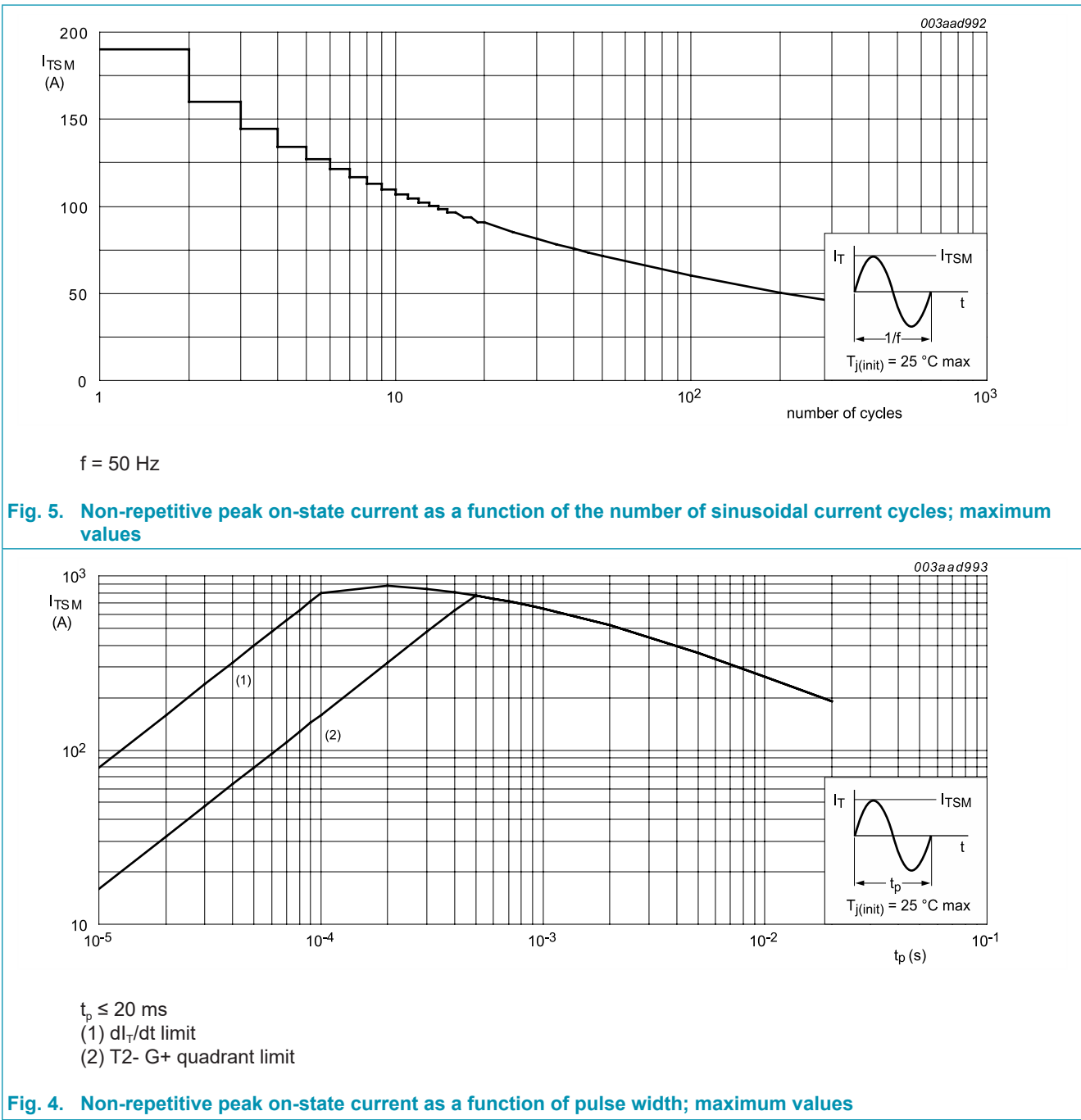


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



$\alpha$  = conduction angle  
 $a$  = form factor =  $I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	full cycle; Fig.6		-	-	1	K/W
		half cycle; Fig.6		-	-	1.4	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	60	-	K/W

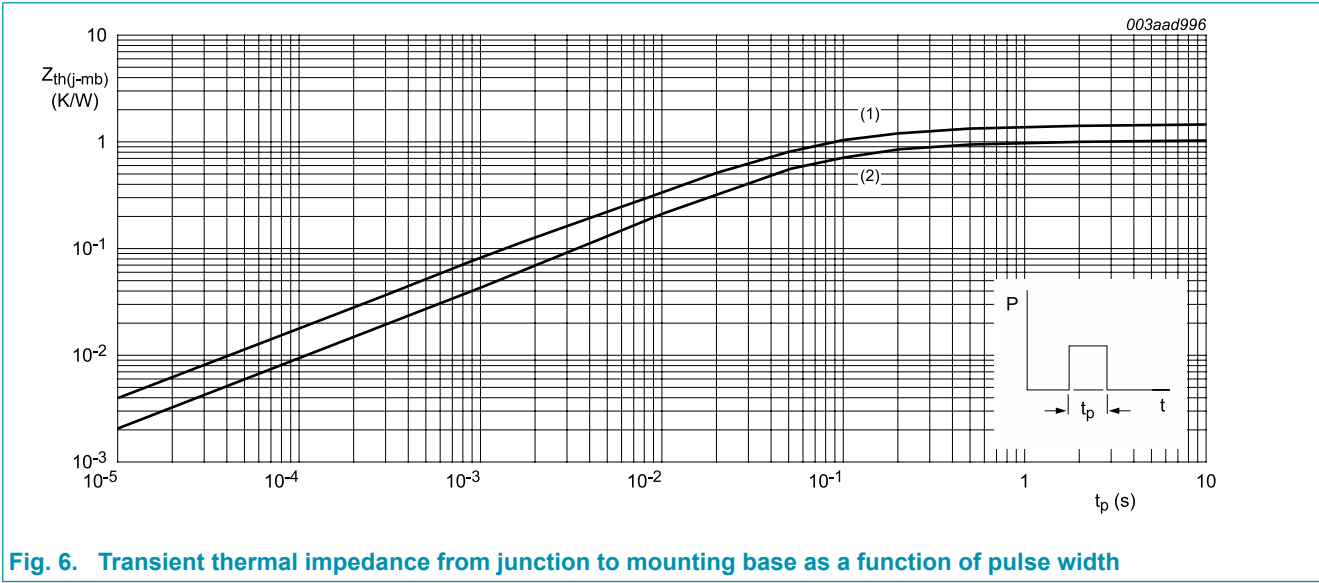
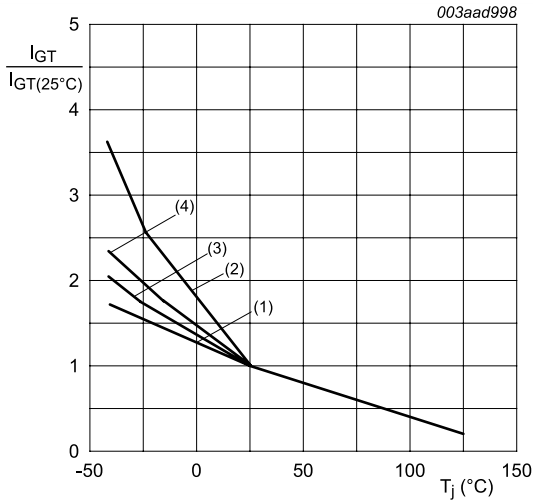


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
<b>Static characteristics</b>							
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>		-	6	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>		-	10	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>		-	11	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; T2- G+; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 7</a>		-	23	70	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G+; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	8	40	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2+ G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	13	60	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G-; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	18	40	mA
		$V_D = 12\text{ V}$ ; $I_G = 0.1\text{ A}$ ; T2- G+; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 8</a>		-	15	60	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; T2+; <a href="#">Fig. 9</a>		-	7	60	mA
		$V_D = 12\text{ V}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; T2-; <a href="#">Fig. 9</a>			12	60	mA
$V_T$	on-state voltage	$I_T = 30\text{ A}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 10</a>		-	1.3	1.55	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 25\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		-	0.7	1	V
		$V_D = 400\text{ V}$ ; $I_T = 0.1\text{ A}$ ; $T_J = 125\text{ }^\circ\text{C}$ ; <a href="#">Fig. 11</a>		0.25	0.4	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_J = 125\text{ }^\circ\text{C}$		-	0.1	0.5	mA
<b>Dynamic characteristics</b>							
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_J = 125\text{ }^\circ\text{C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit		100	300	-	V/ $\mu\text{s}$
$dV_{com}/dt$	rate of change of commutating voltage	$V_D = 400\text{ V}$ ; $T_J = 95\text{ }^\circ\text{C}$ ; $dI_{com}/dt = 9\text{ A/ms}$ ; $I_T = 25\text{ A}$ ; gate open circuit		-	10	-	V/ $\mu\text{s}$
$t_{gt}$	gate-controlled turn-on time	$I_{TM} = 30\text{ A}$ ; $V_D = 800\text{ V}$ ; $I_G = 0.1\text{ A}$ ; $dI_G/dt = 5\text{ A}/\mu\text{s}$		-	2	-	$\mu\text{s}$



- (1) T2+ G+
- (2) T2+ G-
- (3) T2- G-
- (4) T2- G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

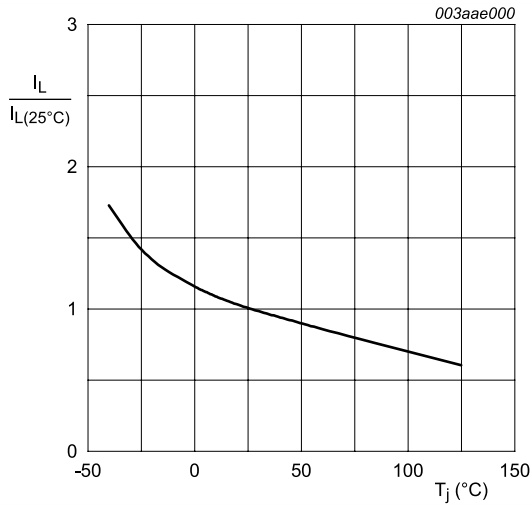


Fig. 8. Normalized latching current as a function of junction temperature

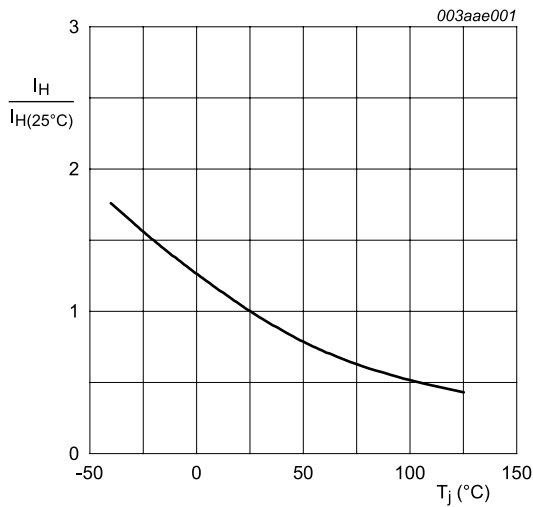
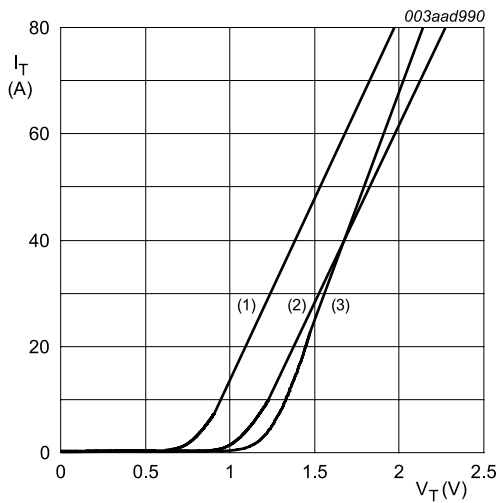


Fig. 9. Normalized holding current as a function of junction temperature



- $V_o = 1.073 \text{ V}$ ;  $R_s = 0.015 \Omega$
- (1)  $T_j = 125^{\circ}\text{C}$ ; typical values
  - (2)  $T_j = 125^{\circ}\text{C}$ ; maximum values
  - (3)  $T_j = 25^{\circ}\text{C}$ ; maximum values

Fig. 10. On-state current as a function of on-state voltage



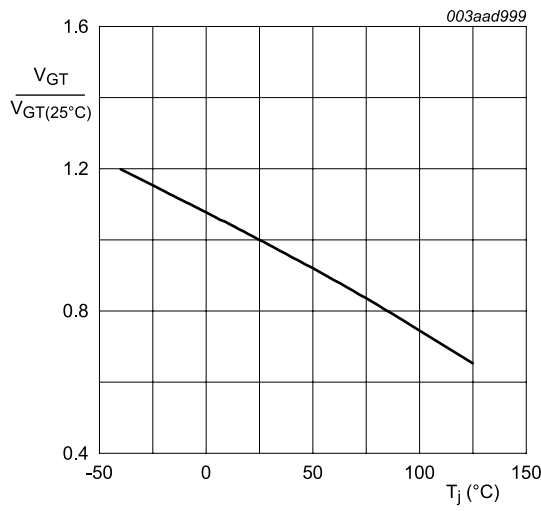
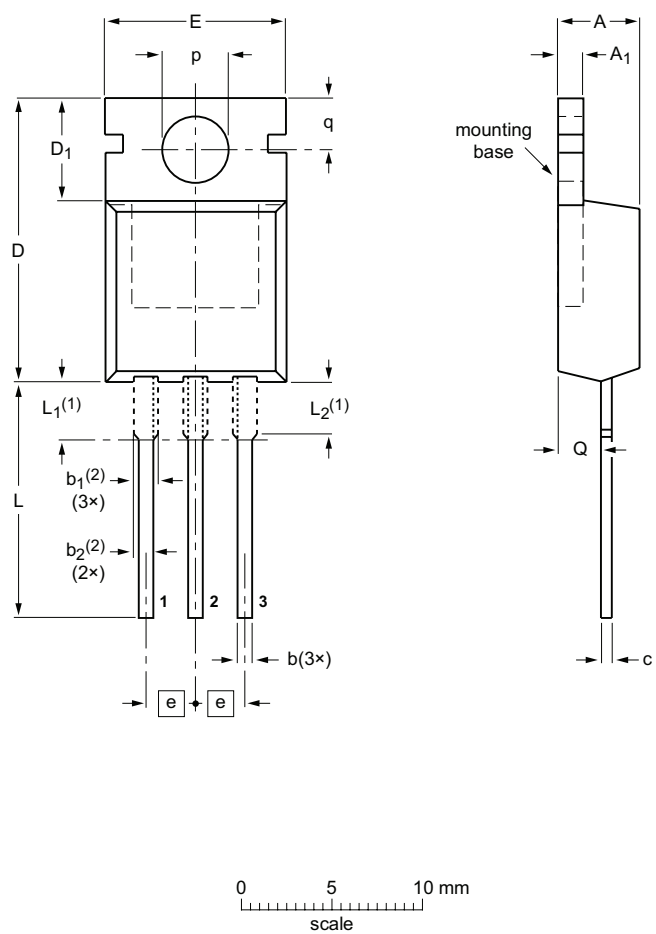


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78



DIMENSIONS (mm are the original dimensions)

UNIT	A	A <sub>1</sub>	b	b <sub>1</sub> (2)	b <sub>2</sub> (2)	c	D	D <sub>1</sub>	E	e	L	L <sub>1</sub> (1)	L <sub>2</sub> (1) max.	p	q	Q
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT78		3-lead TO-220AB	SC-46			08-04-23 08-06-13

## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.ween-semi.com>.

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Date of release: 23 March 2018

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# Products

## BTA140-800






Planar passivated four quadrant triac in a SOT78 (T0-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.


### Features and Benefits

- High blocking voltage capability
- High noise immunity
- Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

### Applications

- General purpose motor controls
- Small loads in washing machines
- Rectifier-fed DC inductive loads e.g. DC motors and solenoids

 Parametric	 Package	 Quality, reliability & chemical content	 Ordering	 Datasheet
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Type number	Package	Packing	Product status	Marking	Orderable part number	Ordering code (12NC)
BTA140-800	 TO220	Horizontal, Rail Pack	Volume production	Standard Marking	BTA140-800,127	9338 156 90127

### Product Lines

Silicon Carbide (SiC)	Wafer
Diodes	Module
Thyristors	Transient Voltage Suppressor (TVS)
Automotive Grade Products	Insulated gate bipolar transistor (IGBT)
Transistors	Electro-Static discharge diodes (ESD)

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